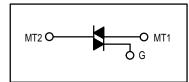
# **Triacs** Silicon Bidirectional Thyristors

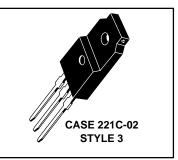
... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 800 Volts
- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Isolated TO-220 Type Package for Ease of Mounting
- Gate Triggering in Three Modes (MAC218FP Series) or Four Modes (MAC218AFP Series)



MAC218FP Series MAC218AFP Series

> ISOLATED TRIACS THYRISTORS 8 AMPERES RMS 200 thru 800 VOLTS



**MAXIMUM RATINGS** (T<sub>J</sub> =  $25^{\circ}$ C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C) (1/2 Sine Wave 50 to 60 Hz, Gate Open) MAC218-4FP, MAC218A4FP MAC218-6FP, MAC218A6FP MAC218-8FP, MAC218A8FP MAC218-10FP, MAC218A10FP	VDRM	200 400 600 800	Volts
On-State RMS Current (T <sub>C</sub> = +80°C) Full Cycle Sine Wave 50 to 60 Hz <sup>(2)</sup>	IT(RMS)	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, preceded and followed by rated current, $T_C = 80^{\circ}C$ )	ITSM	100	Amps
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	40	A <sup>2</sup> s
Peak Gate Power (T <sub>C</sub> = +80°C, Pulse Width = 2 $\mu$ s)	PGM	16	Watts
Average Gate Power (T <sub>C</sub> = +80°C, t = 8.3 ms)	PG(AV)	0.35	Watt
Peak Gate Current (Pulse Width = $1 \mu s$ )	I <sub>GM</sub>	4	Amps
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity $\leq$ 20%)	V(ISO)	1500	Volts
Operating Junction Temperature	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case	R <sub>θ</sub> JC	2.2	°C/W
Thermal Resistance, Case to Sink	R <sub>0CS</sub>	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	60	°C/W

1. VDRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. The case temperature reference point for all T<sub>C</sub> measurements is a point on the center lead of the package as close as possible to the plastic body.



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## **MAC218FP Series MAC218AFP Series**

**ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> =  $25^{\circ}$ C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Off-State Current (Either Direction) ( $V_D$ = Rated $V_{DRM}$ @ $T_J$ = 125°C, Gate Open )	IDRM	-	—	2	mA
Peak On-State Voltage (Either Direction) (I <sub>TM</sub> = 11.3 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle < 2%)	VTM	—	1.7	2	Volts
Gate Trigger Current (Continuous dc) ( $V_D = 12 \text{ Vdc}$ , $R_L = 12 \Omega$ ) Trigger Mode MT2(+), G(+) ; MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	lgt	- - - -	 	50 50 50 75	mA
$ \begin{array}{l} \mbox{Gate Trigger Voltage (Continuous dc)} \\ (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms) \\ MT2(+), G(+) \\ MT2(+), G(-) \\ MT2(-), G(-) \\ MT2(-), G(+) "A" SUFFIX ONLY \\ (Main Terminal Voltage = Rated V_{DRM}, R_L = 10 \ \mbox{k}\Omega, \ \mbox{T}_J = +125^{\circ}\mbox{C}) \\ MT2(+), G(+); \ \mbox{MT2}(-), G(-); \ \mbox{MT2}(+), G(-) \\ MT2(-), G(+) "A" SUFFIX ONLY \\ \end{array} $	V <sub>GT</sub>	   0.2 0.2	0.9 0.9 1.1 1.4 —	2 2 2.5 —	Volts
Holding Current (Either Direction) (V <sub>D</sub> = 24 Vdc, Gate Open, Initiating Current = 200 mA)	ΙΗ	—	—	50	mA
Critical Rate of Rise of Commutating Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, $T_C$ = 80°C)	dv/dt(c)	-	5	-	V/µs
Critical Rate of Rise of Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Voltage Rise, Gate Open, T <sub>J</sub> = 125°C)	dv/dt	—	100	—	V/µs

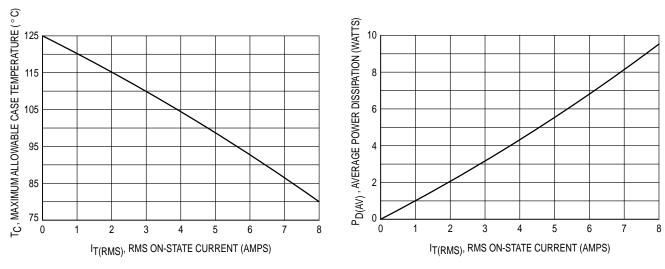


Figure 1. Current Derating



### **TYPICAL CHARACTERISTICS**

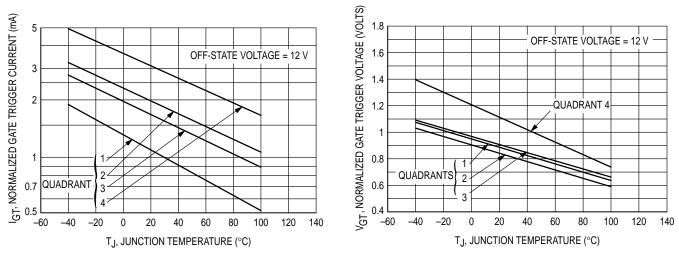


Figure 3. Normalized Gate Trigger Current

Figure 4. Normalized Gate Trigger Voltage

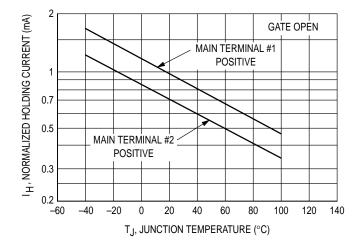
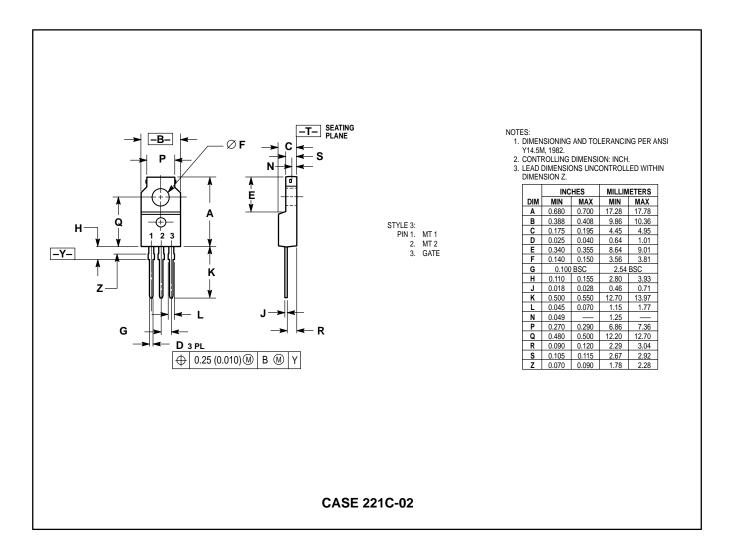


Figure 5. Normalized Holding Current

## PACKAGE DIMENSIONS



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